



General Description

The SIR668DP-T1-RE3 use advanced SGT MOSFET technology to provide low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics.

This device is specially designed to get better ruggedness and suitable.

General Features

$V_{DS} = 100V$ $I_D = 120A$

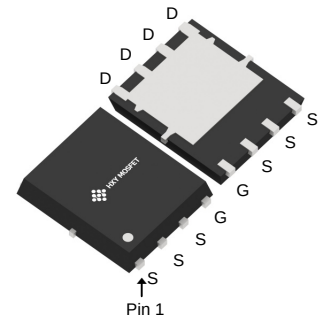
$R_{DS(ON)} < 4.4m\Omega @ V_{GS}=10V$

Applications

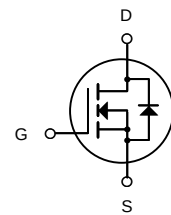
Consumer electronic power supply Motor control

Synchronous-rectification Isolated DC

Synchronous-rectification applications



DFN5X6-8L



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SIR668DP-T1-RE3	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ¹	120	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ¹	81	A
I_{DM}	Pulsed Drain Current ²	512	A
EAS	Single Pulse Avalanche Energy ³	486	mJ
I_{AS}	Avalanche Current	67	A
$P_D @ T_c = 25^\circ C$	Total Power Dissipation ⁴	176	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JC}$	Thermal Resistance from Junction-to-Ambient ³	0.8	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	56	$^\circ C/W$



Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	---	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	---	3.6	4.4	mΩ
		V _{GS} =4.5V, I _D =20A	---	---	---	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2.0	3.0	4.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	---	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =100°C	---	---	100	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =20A	---	35	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.6	---	Ω
Q _g	Total Gate Charge	V _{DS} =50V, V _{GS} =10V, I _D =20A	---	69	---	nC
Q _{gs}	Gate-Source Charge		---	24	---	
Q _{gd}	Gate-Drain Charge		---	18.5	---	
T _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DD} =50V, R _G =3Ω, I _D =20A	---	18.0	---	ns
T _r	Rise Time		---	23	---	
T _{d(off)}	Turn-Off Delay Time		---	37	---	
T _f	Fall Time		---	15.7	---	
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	---	4102	---	pF
C _{oss}	Output Capacitance		---	592	---	
C _{rss}	Reverse Transfer Capacitance		---	19.8	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	120	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is T_J = 25°C, L = 3.0mH, I_{AS} = 18A, V_{GS} = 10V, V_{DD} = 50V; 100% test at L = 0.1mH, I_{AS} = 67A.
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



Typical Characteristics

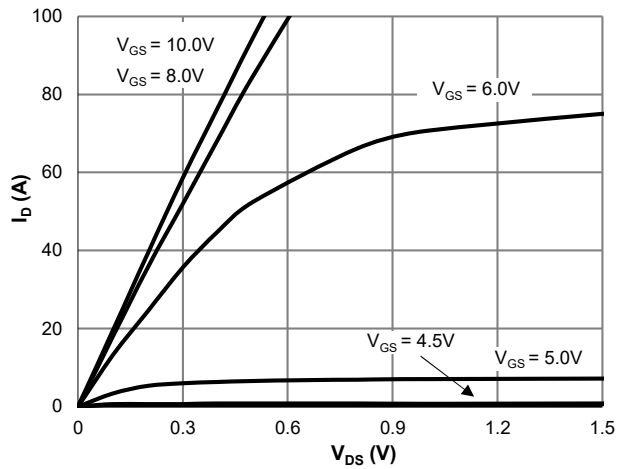


Figure 1: Saturation Characteristics

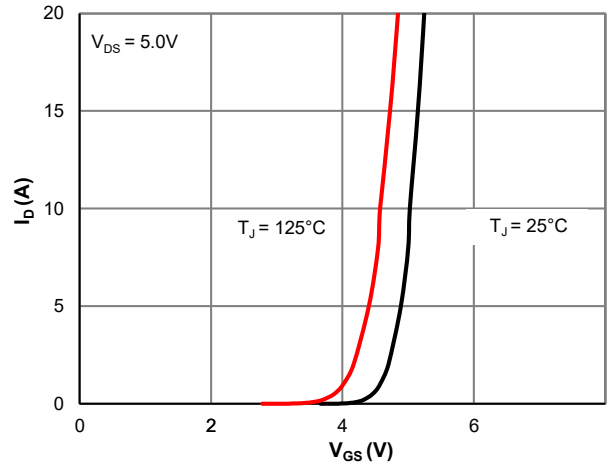


Figure 2: Transfer Characteristics

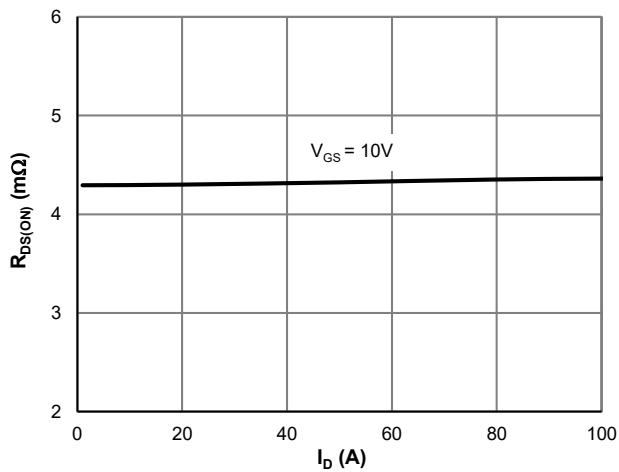


Figure 3: $R_{DS(ON)}$ vs. Drain Current

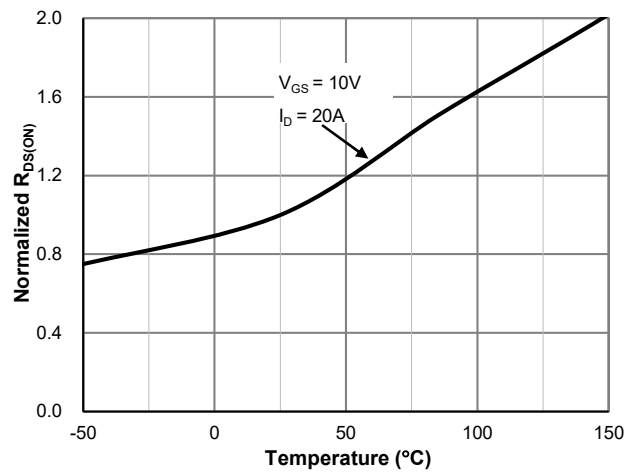


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

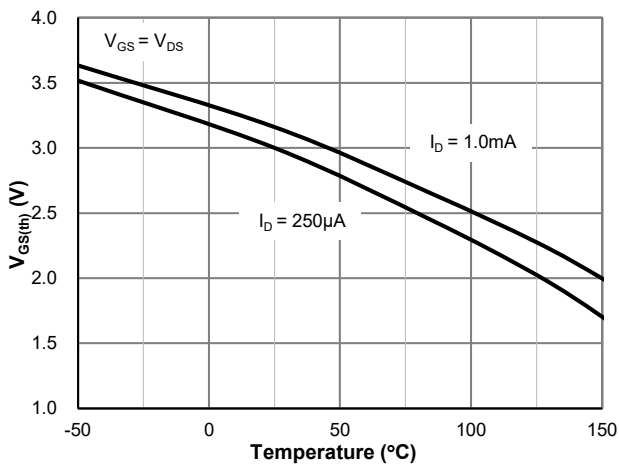


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

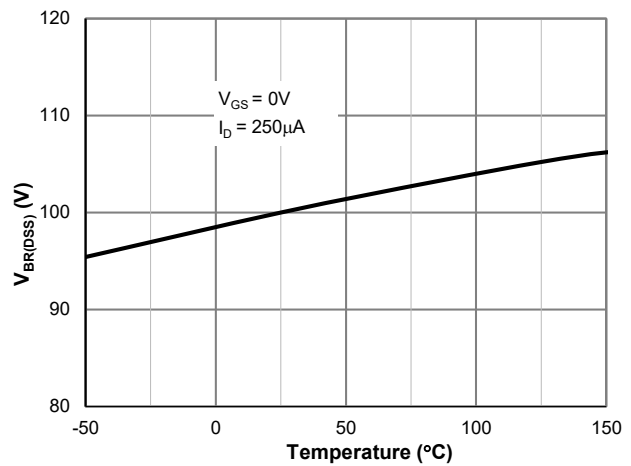


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

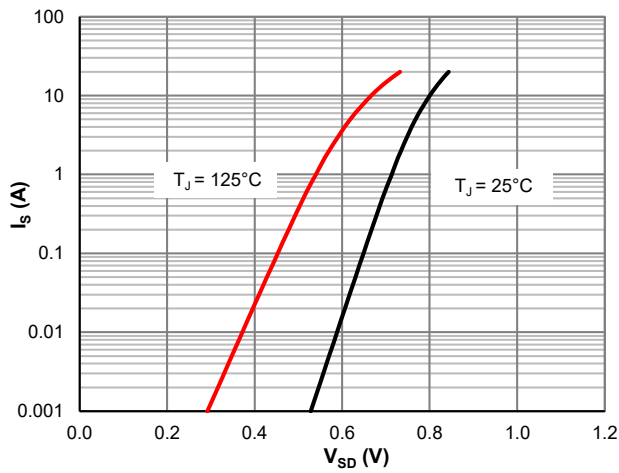


Figure 7: Body-Diode Characteristics

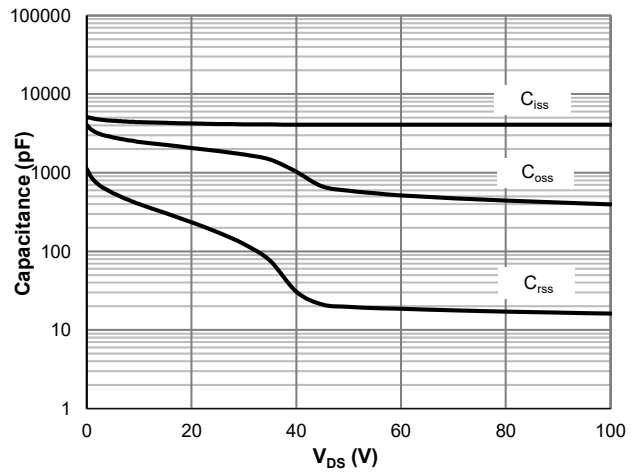


Figure 8: Capacitance Characteristics

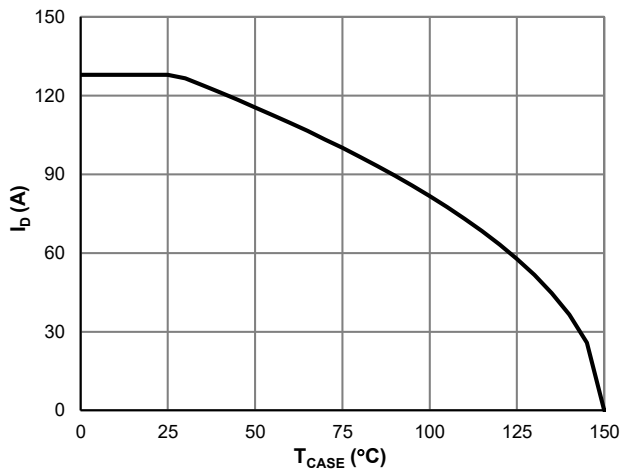


Figure 9: Current De-rating

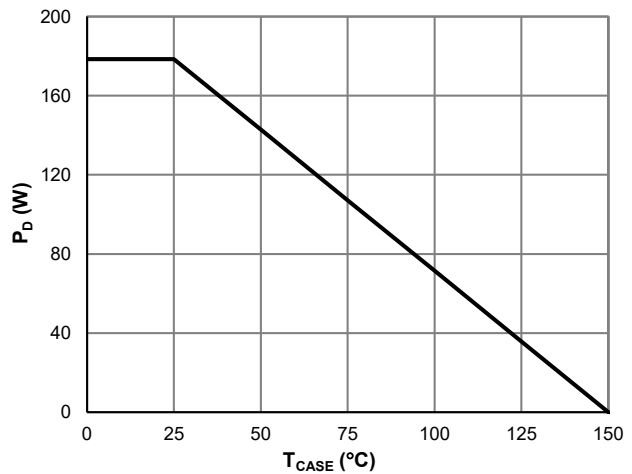


Figure 10: Power De-rating

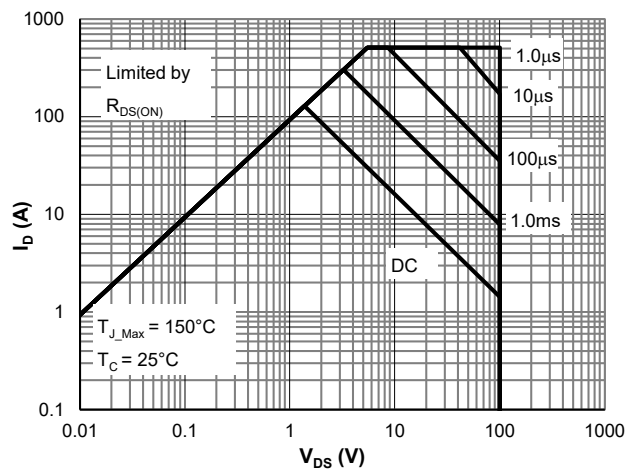


Figure 11: Maximum Safe Operating Area

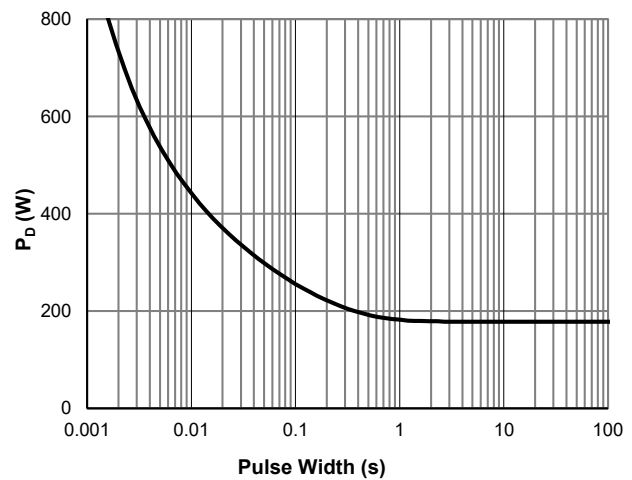


Figure 12: Single Pulse Power Rating, Junction-to-Case

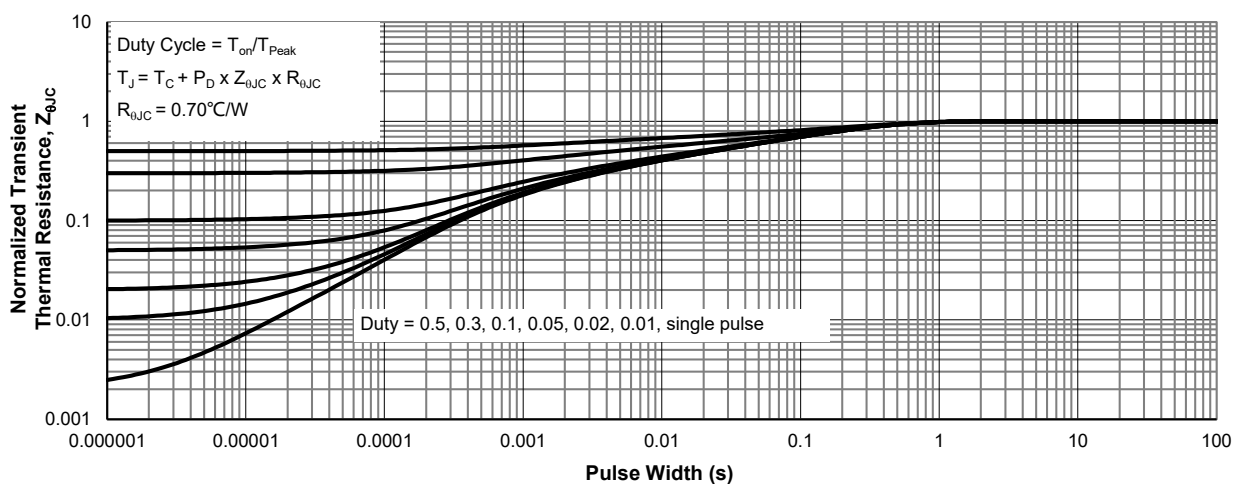
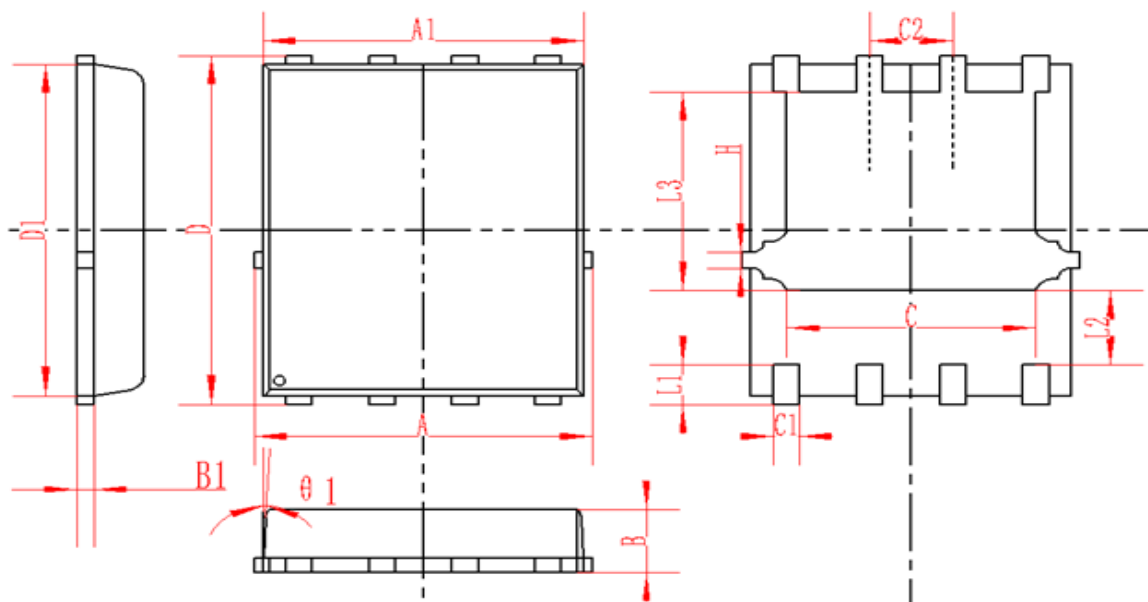


Figure 13: Normalized Maximum Transient Thermal Impedance



DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010



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